

ABSTRACT

A task is to provide a simple method for obtaining a bipolar transistor being free of current gain dispersion and having a lowered base
5 resistance.

The method of the present invention comprises forming a base layer on a semiconductor substrate, and then forming in an insulating film stacked on the base layer a base electrode lead opening and an emitter electrode lead opening at the same time, and subsequently
10 forming a base electrode lead portion and an emitter electrode lead portion in, respectively, the base electrode lead opening and the emitter electrode lead opening.